HD Communications Corp.

HD33768
SOLID STATE HIGH POWER AMPLIFIER



FEATURES

Class A/AB linear GaN design
Instantaneous ultra-wide bandwidth
Rack mounted system
Designed for broadband EMI/RFI, Lab, Comm. and EW applications
Suitable for all single channel modulation standards
Built-in protection circuits
High reliability and ruggedness

ELECTRICAL SPECIFICATIONS: 50Ω, 25°C

Parameter	Specification	Notes
Operating Frequency Range	100 - 500 MHz	
Power Output @ Psat	500 Watt Min	Pin=0dBm for rated Pout
Power Gain	57 dB Min	
Power Gain Flatness	4 dB p-p Max	Constant input power
Gain Variation Over Temperature	±2.0 dB Max	
Input / Output Return Loss	-10 dB Max	Relative to 50 Ohm
2-Tone Intermodulation (IMD)	-30 dBc Typ	44dBm/Tone, Δ = 1MHz
Harmonics	-20 dBc	-30dBc with optional LPF
Spurious	-60 dBc Max	Non-harmonic
Operating Voltage	180 - 240 VAC	
Power Consumption	2500 Watt Max	At rated output
Input Power Protection	+5 dBm Max	<10 Sec without damage
Load VSWR Protection	10 : 1 Max	<1 minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Ambient Temperature	0 to +50 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

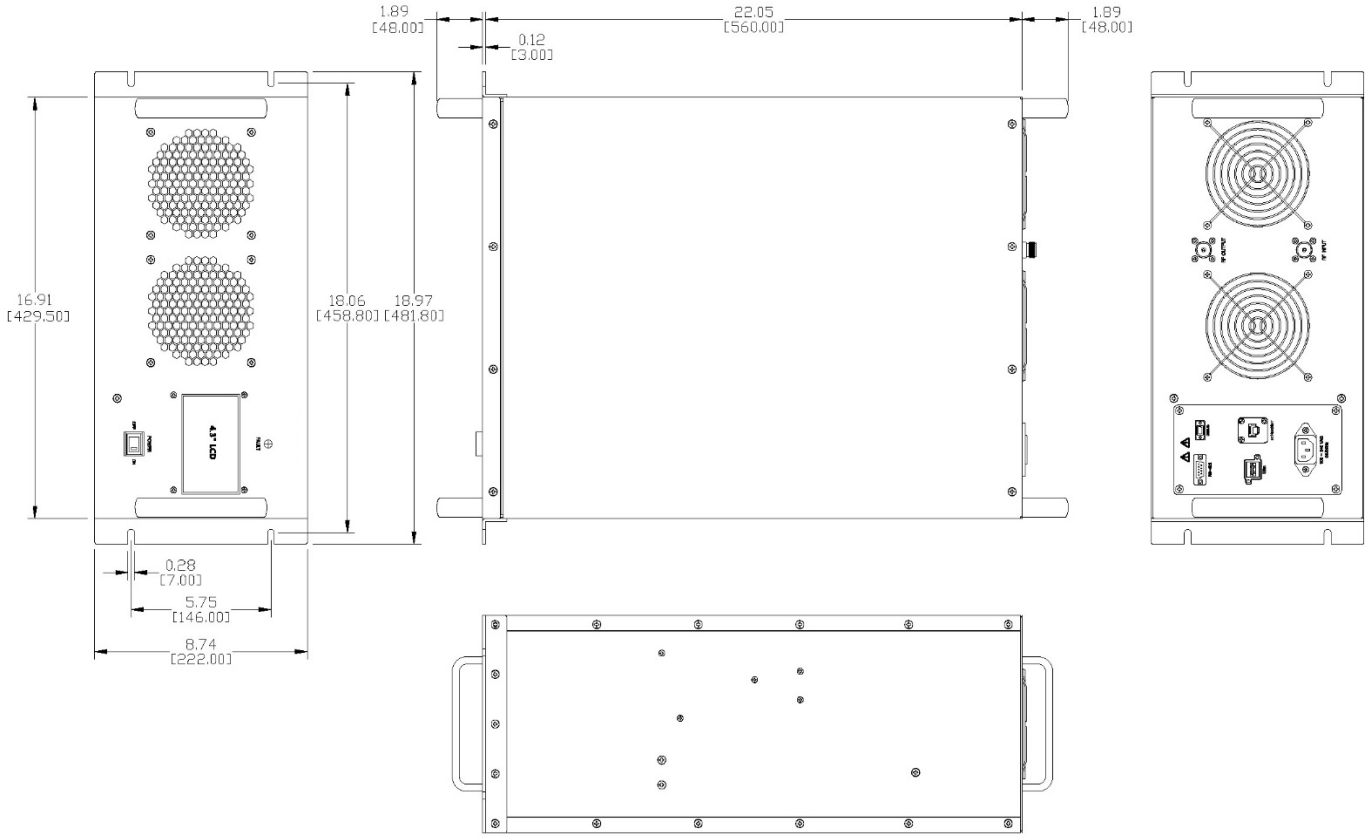
Parameter	Specification	Notes
Dimensions W x H x D	425 x 222 x D mm	5U - excluding handles
Weight	53 Kg.	
RF Connectors In/Out	Type-N Female	
AC Power	IEC 60320-C14 / 9-Pin D-Sub	Or equivalent
Cooling	60dBa-Typ- Air-Liquid Cooled	Built in pump (closed loop)
OPTIONAL: Digital Monitor & Control FWD, REV, VSWR, GAIN, ALC, V & I, TEMP	Ethernet RJ-45 TCP/IP, RS422/485, USB Optional GPIB Interface	Optional Remote Bluetooth application

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OUTLINE DRAWING



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